2SC3179

Silicon NPN Triple Diffused Planar Transistor (Complement to type 2SA1262)

Application : Audio and General Purpose

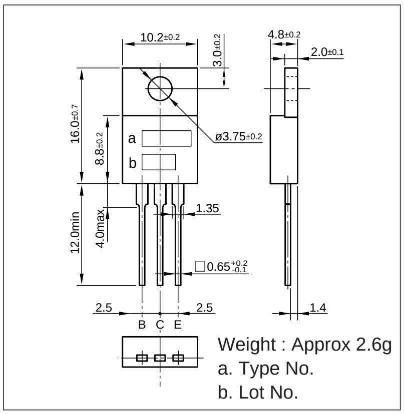
Absolute maximum ratings (Ta=25°C)

Symbol	2SC3179	Unit
V_{CBO}	80	V
V_{CEO}	60	V
V_{EBO}	6	V
I_C	4	A
I_B	1	A
P_C	30(Tc=25°C)	W
Tj	150	°C
Tstg	–55 to +150	°C

Electrical Characteristics (Ta=25°C)

Symbol	Conditions	2SC3179	Unit
I_{CBO}	V_{CB}=80V	100max	μA
I_{EBO}	V_{EB}=6V	100max	μA
$V_{(BR)CEO}$	I_C=25mA	60min	V
h_{FE}	V_{CE}=4V, I_C=1V	40min	
$V_{CE(sat)}$	I_C=2A, I_B=0.2A	0.6max	V
f_T	V_{CE}=12V, I_E=–0.2A	15typ	MHz
C_{OB}	V_{CB}=10V, f=1MHz	60typ	pF

External Dimensions MT-25(TO220)

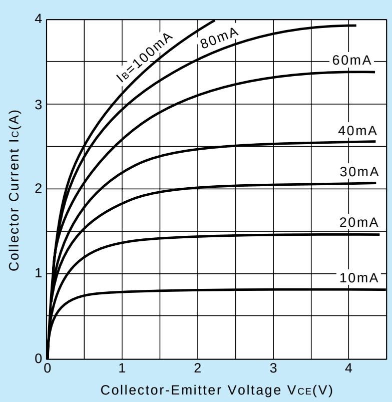


Weight : Approx 2.6g
a. Type No.
b. Lot No.

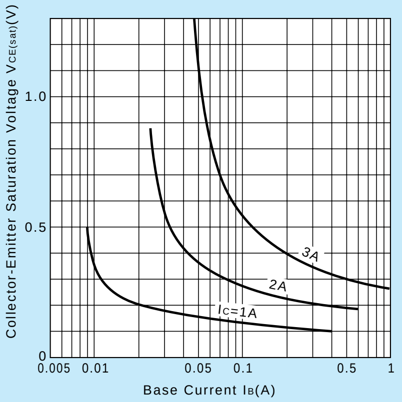
Typical Switching Characteristics (Common Emitter)

V_{CC} (V)	R_L (Ω)	I_C (A)	V_{BB1} (V)	V_{BB2} (V)	I_{B1} (mA)	I_{B2} (mA)	ton (μs)	tstg (μs)	tf (μs)
20	10	2	10	–5	200	–200	0.2typ	1.9typ	0.29typ

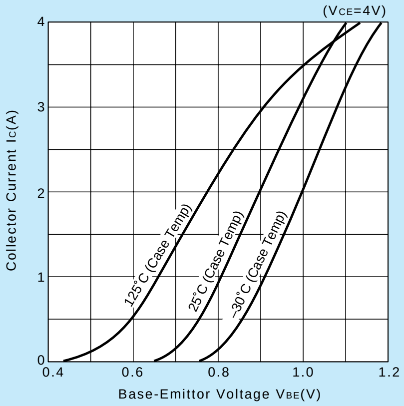
I_C–V_{CE} Characteristics (Typical)



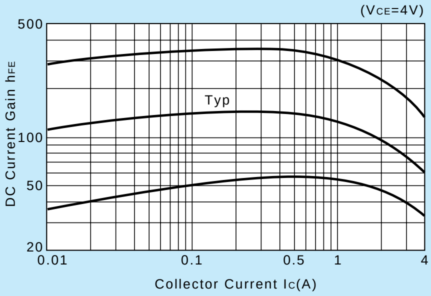
$V_{CE(sat)}$–I_B Characteristics (Typical)



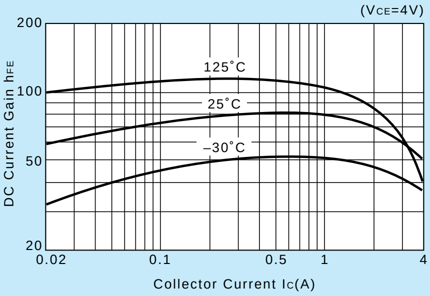
I_C–V_{BE} Temperature Characteristics (Typical)



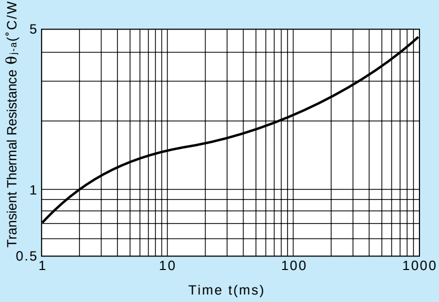
h_{FE}–I_C Characteristics (Typical)



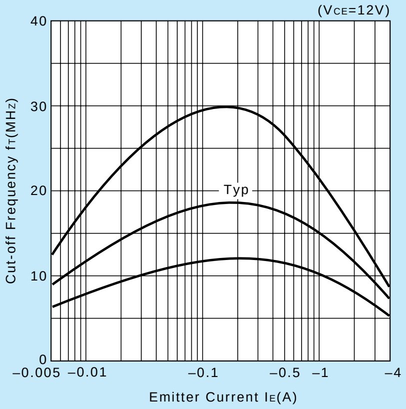
h_{FE}–I_C Temperature Characteristics (Typical)



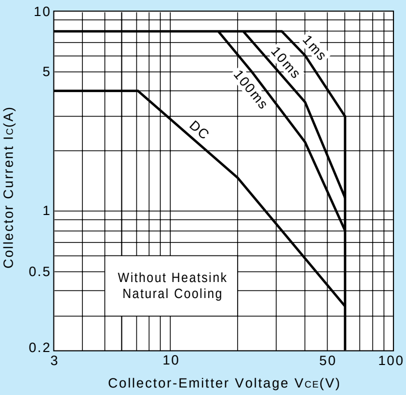
θ_{j-a}–t Characteristics



f_T–I_E Characteristics (Typical)



Safe Operating Area (Single Pulse)



Pc–Ta Derating